

## IN THE TITLE

Please delete the title in its entirety and insert --- A DEVICE HAVING RECESSED SPACERS FOR IMPROVED SALICIDE RESISTANCE ON POLYSILICON GATES --- therein.

## IN THE CLAIMS

Please cancel claim 9 without prejudice.

Please amend the following claims:

Sub  
C1

8. (Amended) A gate electrode [formed on a substrate] comprising:

[an insulative layer formed on a substrate;]  
a gate layer disposed above a substrate [formed on the insulative layer];  
[a conductive layer formed on the gate layer;]  
thin first spacers disposed [formed] adjacent to opposite sides of said [the] gate layer, wherein tops of said [the] thin first spacers are [recessed] at approximately the same height as top of said gate layer; [and,]  
thick second spacers disposed [formed] adjacent to each of said [the] thin first spacers, said thick second spacers having a flat upper surface, wherein tops of said [the] thick second spacers are [recessed] at approximately the same height as top of said gate layer; and  
a conductive layer disposed on said gate layer, said conductive layer extending beyond edges of said gate layer.

b1

Sub  
D2

10. (Amended) The gate electrode of claim 9 wherein said [the] gate layer  
comprises [is a] polysilicon.

or

11. (Amended) The gate electrode of claim 10 wherein said [the] conductive  
layer comprises [is a] polycide.

12. (Amended) The gate electrode of claim 11 wherein said [the] thin first  
spacers comprise [are an] oxide.

13. (Amended) The gate electrode of claim 12 wherein said [the] thick second  
spacers comprise [are a] nitride.

Sub  
D3

14. (Amended) The gate electrode of claim 13 wherein said [the] polycide  
comprises [is] titanium salicide (TiSi<sub>2</sub>).